CLAIMS

What is claimed is:

- 1 1. A method comprising:
- 2 introducing an interconnection element coupled to a
- 3 substrate, the interconnection element comprising a first
- 4 element material and a second element material;
- 5 releasing the interconnection element from the
- 6 substrate at one end; and
- 7 transforming a property of one of the first element
- 8 material and the second element material to modify the shape
- 9 of the interconnection element.
- 1 2. The method of claim 1, wherein transforming comprises
- 2 transforming the property of each of the first element
- 3 material and the second element material.
- 1 3. The method of claim 1, wherein the interconnection
- 2 element is released from the substrate before the
- 3 transformation.
- 1 4. The method of claim 1, wherein transforming comprises
- 2 heating the interconnection element.
- 1 5. The method of claim 1, wherein transforming comprises
- 2 changing a volume of one of the first element material and
- 3 the second element material.
- 1 6. The method of claim 1, wherein transforming comprises
- 2 biasing an end of the interconnection element from a first
- 3 position to a second position that is a greater distance
- 4 from a surface of the substrate.
- 1 7. The method of claim 6, further comprising limiting the
- 2 transformation bias of the end of the interconnection
- 3 element.

- 1 8. The method of claim 6, wherein the transformable
- 2 property comprises stress and transforming comprises
- 3 reducing the magnitude of the stress.
- 1 9. The method of claim 6, further comprising:
- 2 introducing a third element material having a resilient
- 3 property over the interconnection element.
- 1 10. The method of claim 9, wherein the interconnection
 - 2 element is coupled to a surface of the substrate and the
 - 3 third element material is introduced over a surface of the
- 4 interconnection element opposite the substrate surface, the
- 5 method of introducing the third element material comprising:
- 6 patterning a masking material over the substrate to
- 7 have an opening exposing the surface of the interconnection
- 8 element; and
- 9 introducing the third element material to the exposed
- 10 surface of the interconnection element.
- 1 11. The method of claim 10, wherein the third material is
- 2 an electrophoretic resist material.
- 1 12. The method of claim 10, wherein the spring element
- 2 material is introduced by a plating process.
- 1 13. The method of claim 5, wherein the second element
- 2 material is coupled to the first element material at a side
- 3 opposite the substrate and the second element material
- 4 comprises the transformable property, the method further
- 5 comprising:
- 6 after transforming the property, removing the second
- 7 element material.
- 1 14. The method of claim 13, wherein the second element
- 2 material comprises a shape memory alloy and creating an

- 3 interconnection element comprises introducing the second
- 4 element material in a martinsite state and transforming a
- 5 property of the second element material comprises
- 6 transforming the second element material to a memory state,
- 7 the second element material having a volume in its memory
- 8 state that is different than a volume in its martinsite
- 9 state.
- 1 15. The method of claim 14, wherein after transforming the
- 2 property, the method further comprising:
- 3 annealing the interconnection element.
- 1 16. The method of claim 1, further comprising:
- 2 after transforming, coupling the substrate to contact
- 3 nodes on an electronic component at the released end of the
- 4 interconnection element.
- 1 17. The method of claim 16, further comprising:
- 2 after coupling, testing one of the substrate and the
- 3 electronic component.
- 1 18. The method of claim 17, wherein the electronic
- 2 component comprises a die and the released end of the
- 3 interconnection element is coupled to a bond pad of the die.
- 1 19. A method, comprising:
- 2 patterning a masking material over a substrate having
- 3 an opening to a contact node formed on the substrate;
- 4 creating an interconnection element having a base
- 5 coupled to the contact node and a free end extending over a
- 6 portion of the masking material, the interconnection element
- 7 comprising a first element material and a second element
- 8 material;
- 9 removing the masking material; and

- transforming a property of one of the first element
- 11 material and the second element material of the
- 12 interconnection element to modify the shape of the
- 13 interconnection element.
- 1 20. The method of claim 19, wherein transforming comprises
- 2 transforming each of the first element material and the
- 3 second element material.
- 1 21. The method of claim 19, wherein transforming comprises
- 2 heating the interconnection element to a temperature.
- 1 22. The method of claim 19, wherein transforming produces a
- 2 volume change in one of the first element material and the
- 3 second element material.
- 1 23. The method of claim 19, wherein the transformable
- 2 property comprises stress and transforming comprises
- 3 modifying the magnitude of the stress.
- 1 24. The method of claim 19, wherein the transformation
- 2 biases the free end of the interconnection element from a
- 3 first position to a second position that is a greater
- 4 distance from a surface of the substrate.
- 1 25. The method of claim 24, further comprising limiting the
- 2 transformation bias of the free end of the interconnection
- 3 element.
- 1 26. The method of claim 19, further comprising:
- 2 introducing a third element material having a resilient
- 3 property over the interconnection element.
- 1 27. The method of claim 26, wherein the introduction of the
- 2 third element material comprises electroplating a conductive
- 3 alloy.

- 1 28. The method of claim 26, wherein the interconnection
- 2 element is coupled to a surface of the substrate and the
- 3 third element material is introduced over a surface of the
- 4 interconnection element opposite the substrate surface, the
- 5 method of introducing the third element material comprising:
- 6 patterning a masking material over the substrate to
- 7 have an opening exposing the surface of the interconnection
- 8 element; and
- 9 introducing the third element material to the exposed
- 10 surface of the interconnection element.
- 1 29. The method of claim 28, wherein the masking material is
- 2 an electrophoretic resist material.
- 1 30. The method of claim 28, wherein the third element
- 2 material is introduced by electroplating.
- 3 31. The method of claim 19, wherein the second element
- 4 material is coupled to the first element material at a side
- 5 opposite the substrate and the second element material
- 6 comprises the transformable property, the method further
- 7 comprising:
- 8 after transforming the property, removing the second
- 9 element material.
- 10 32. The method of claim 31, wherein the second element
- 11 material comprises a shape memory alloy and creating an
- 12 interconnection element comprises introducing the second
- 13 element material in a martinsite state and transforming a
- 14 property of the second element material comprises
- 15 transforming the second element material to a memory state,
- 16 the second element material having a volume in its memory
- 17 state that is different than a volume in its martinsite
- 18 state.

- 1 33. The method of claim 32, wherein after transforming the
- 2 property, the method further comprising:
- 3 annealing the interconnection element.
- 1 34. The method of claim 19, prior to creating an
- 2 interconnection element, re-distributing the contact node
- 3 from a first contact point on the substrate to a different
- 4 second contact point on the substrate and creating the
- 5 interconnection comprises coupling the base at the second
- 6 contact point.
- 1 35. The method of claim 19, further comprising:
- 2 after transforming, coupling the substrate to contact
- 3 nodes on an electronic component at the released end of the
- 4 interconnection element.
- 1 36. The method of claim 35, further comprising:
- 2 after coupling, testing one of the substrate and the
- 3 electronic component.
- 1 37. The method of claim 36, wherein the electronic
- 2 component comprises a die and the released end of the
- 3 interconnection element is coupled to a bond pad of the die.
- 1 38. A method comprising:
- 2 forming an interconnection element on a surface of a
- 3 first substrate, the interconnection element comprising a
- 4 first element material and a second element material and a
- 5 base end coupled to a contact node on the first substrate
- 6 and a free end;
- 7 transforming a property of one of the first element
- 8 material and the second element material to modify the shape
- 9 of the interconnection element; and
- 10 coupling the interconnection element at the free end to
- 11 a contact node on a second substrate.

- 1 39. The method of claim 38, wherein forming the
- 2 interconnection element comprises forming a plurality of
- 3 interconnection elements coupled to corresponding contact
- 4 nodes on the first substrate and coupling the
- 5 interconnection element comprises coupling the plurality of
- 6 interconnection elements to corresponding contact nodes on
- 7 the second substrate.
- 1 40. The method of claim 39, wherein coupling comprises
- 2 bringing the free ends of the plurality of interconnection
- 3 elements together with corresponding contact nodes with a
- 4 sufficient contact force to make a pressure connection.
- 1 41. The method of claim 39, wherein the plurality of
- 2 interconnection elements comprise first interconnection
- 3 elements coupled to corresponding first contact nodes on a
- 4 first surface of the first substrate and second
- 5 interconnection elements coupled to corresponding second
- 6 contact nodes on a second surface of the first substrate,
- 7 wherein the first interconnection elements are coupled
- 8 to the contact nodes on the second substrate.
- 1 42. The method of claim 41, further comprising coupling the
- 2 second interconnection elements to corresponding contact
- 3 nodes of a third substrate in an interposer application.
- 1 43. The method of claim 39, further comprising testing the
- 2 second substrate.
- 1 44. The method of claim 39, wherein the second substrate is
- 2 a circuit board,
- 1 45. The method of claim 39, wherein the contact nodes of
- 2 the second substrate comprise external connection points,
- 3 the method further comprising:

- 4 coupling the external connection points of the second
- 5 substrate to corresponding contact nodes of a third
- 6 substrate.
- 1 46. The method of claim 39, wherein coupling comprises a
- 2 temporary connection to the second substrate.
- 1 47. The method of claim 39, wherein coupling comprises a
- 2 permanent connection to the second substrate.
- 1 48. The method of claim 47, wherein coupling comprises
- 2 soldering the free ends of the interconnection elements to
- 3 the corresponding contact nodes of the second substrate.
- 1 49. The method of claim 39, wherein the second substrate is
- 2 part of a system.
- 1 50. The method of claim 49, wherein the system comprises
- 2 one of an integrated circuit test system and a substrate
- 3 system.